

GP 2822



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Leonard Forbes

Title: SILICON-GERMANIUM DEVICES FOR CMOS FORMED BY ION IMPLANTATION AND SOLID PHASE EPITAXIAL REGROWTH

Docket No.: 303.229US2

Serial No.: 09/132,157

Filed: August 11, 1998

Due Date: October 18, 2000

Examiner: Mark V. Prenty

Group Art Unit: 2822

Commissioner for Patents
Washington, D.C. 20231

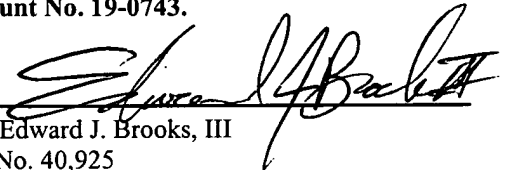
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We are transmitting herewith the following attached items (as indicated with an "X"):

- X A return postcard.
- X An Amendment and Response (8 Pages).

Please consider this a **PETITION FOR EXTENSION OF TIME** for sufficient number of months to enter these papers and please charge any additional required fees or credit overpayment to Deposit Account No. 19-0743.

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CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this correspondence is being deposited with the United States Postal Service with sufficient postage as first class mail, in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231, on this 18 day of October, 2000.

Amy Moriarty
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SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.
(GENERAL)

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PATENT

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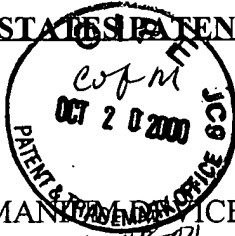
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#3016
10-26-00
R. D. Duder

AMENDMENT AND RESPONSE UNDER 37 CFR § 1.111

Commissioner for Patents
Washington, D.C. 20231

Applicant has reviewed the Office Action mailed on July 18, 2000. Please amend the above-identified patent application as follows.

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IN THE CLAIMS

Please amend the claims as follows:

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- Sub H1
11. (Four times amended) A p-channel metal-oxide-semiconductor transistor, comprising:
- a silicon substrate;
 - a gate oxide, coupled to the substrate;
 - a gate, coupled to the gate oxide;
 - source/drain regions formed in the substrate on opposite sides of the gate; and
 - a $\text{Si}_{1-x}\text{Ge}_x$ channel region, having a germanium molar fraction of x , and formed in the substrate, underneath and adjoining the gate oxide and between the source/drain regions;
- wherein the $\text{Si}_{1-x}\text{Ge}_x$ channel region [is formed subsequent to formation of the gate oxide.] has a channel length less than $7\mu\text{m}$.
- G1

- Sub H2
24. (Four times amended) A p-channel metal-oxide-semiconductor transistor formed on a silicon substrate, comprising:
- a $\text{Si}_{1-x}\text{Ge}_x$ channel region, having a germanium molar fraction of x , and formed in the substrate, underneath and adjoining a gate oxide and between a source region and a drain region;
- G2